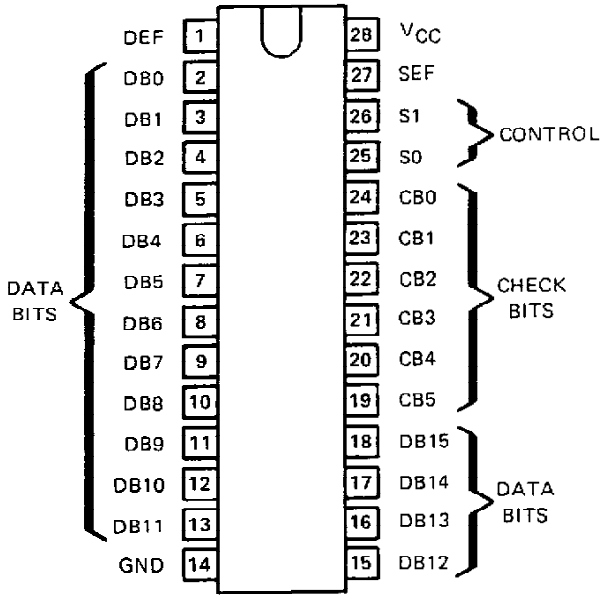
SN54LS630, SN54LS631, SN74LS630, SN74LS631
16-BIT PARALLEL ERROR DETECTION AND CORRECTION CIRCUITS

SDLS187
D2550, MARCH 1980

(TIM99630, TIM99631)

- Detects and Corrects Single-Bit Errors
- Detects and Flags Dual-Bit Errors
- Fast Processing Times:
  - Write Cycle: Generates Check Word in 45 ns Typical
  - Read Cycle: Flags Errors in 27 ns Typical
- Power Dissipation 600 mW Typical
- Choice of Output Configurations:
  - 'LS630 . . . 3-State
  - 'LS631 . . . Open-Collector

SN54LS' . . . JD PACKAGE
SN74LS' . . . JD OR N PACKAGE
(TOP VIEW)



description

The 'LS630 and 'LS631 devices are 16-bit parallel error detection and correction circuits (EDACs) in 28-pin, 600-mil packages. They use a modified Hamming code to generate a 6-bit check word from a 16-bit data word. This check word is stored along with the data word during the memory write cycle. During the memory read cycle, the 22-bit words from memory are processed by the EDACs to determine if errors have occurred in memory.

Single-bit errors in the 16-bit data word are flagged and corrected.

Single-bit errors in the 6-bit check word are flagged, and the CPU sends the EDAC through the correction cycle even though the 16-bit word is not in error. The correction cycle will simply pass along the original 16-bit word in this case and produce error syndrome bits to pinpoint the error-generating location.

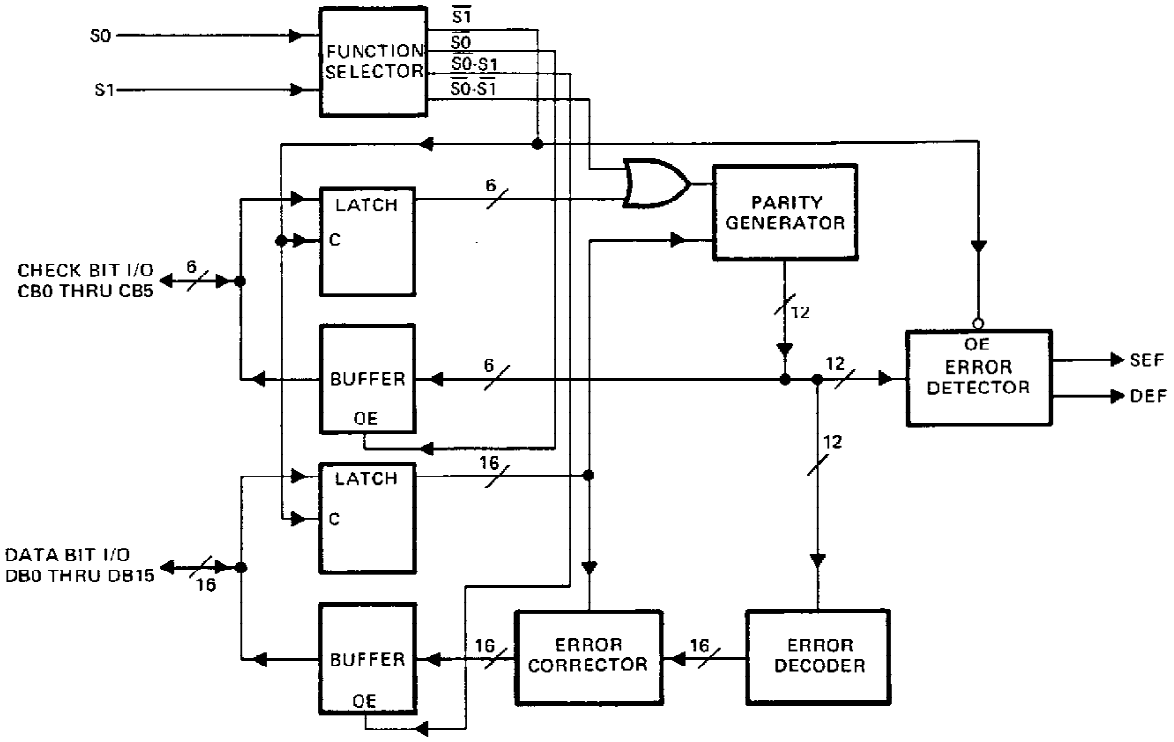
Dual-bit errors are flagged but not corrected. These dual errors may occur in any two bits of the 22-bit word from memory (two errors in the 16-bit data word, two errors in the 6-bit check word, or one error in each word).

The gross-error condition of all lows or all highs from memory will be detected. Otherwise, errors in three or more bits of the 22-bit word are beyond the capabilities of these devices to detect.

CONTROL FUNCTION TABLE

Memory Cycle	Control S1	Control S0	EDAC Function	Data I/O	Check Word I/O	Error Flags SEF	Error Flags DEF
WRITE	L	L	Generate Check Word	Input Data	Output Check Word	L	L
READ	L	H	Read Data & Check Word	Input Data	Input Check Word	L	L
READ	H	H	Latch & Flag Errors	Latch Data	Latch Check Word	Enabled	
READ	H	L	Correct Data Word & Generate Syndrome Bits	Output Corrected Data	Output Syndrome Bits	Enabled	

functional block diagram



ERROR FUNCTION TABLE

Total Number of Errors		Error Flags		Data Correction
16-Bit Data	6-Bit Checkword	SEF	DEF	
0	0	L	L	Not Applicable
1	0	H	L	Correction
0	1	H	L	Correction
1	1	H	H	Interrupt
2	0	H	H	Interrupt
0	2	H	H	Interrupt

In order to be able to determine whether the data from the memory is acceptable to use as presented to the bus, the EDAC must be strobed to enable the error flags and the flags will have to be tested for the zero condition.

The first case in the error function table represents the normal, no-error condition. The CPU sees lows on both flags. The next two cases of single-bit errors require data correction. Although the EDAC can discern the single check bit error and ignore it, the error flags are identical to the single error in the 16-bit data word. The CPU will ask for data correction in both cases. An interrupt condition to the CPU results in each of the last three cases, where dual errors occur.

error detection and correction details

During a memory write cycle, six check bits (CB0-CB5) are generated by eight-input parity generators using the data bits as defined below. During a memory read cycle, the 6-bit check word is retrieved along with the actual data.

CHECKWORD	16-BIT DATA WORD															
BIT	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
CB0	x	x		x	x				x	x	x			x		
CB1	x		x	x		x	x		x			x			x	
CB2		x	x		x	x		x		x			x			x
CB3	x	x	x				x	x			x	x	x			
CB4				x	x	x	x	x						x	x	x
CB5									x	x	x	x	x	x	x	x

The six check bits are parity bits derived from the matrix of data bits as indicated by "x" for each bit.

Error detection is accomplished as the 6-bit check word and the 16-bit data word from memory are applied to internal parity generators/checkers. If the parity of all six groupings of data and check bits are correct, it is assumed that no error has occurred and both error flags will be low. (It should be noted that the sense of two of the check bits, bits CB0 and CB1, is inverted to ensure that the gross-error condition of all lows and all highs is detected.)

If the parity of one or more of the check groups is incorrect, an error has occurred and the proper error flag or flags will be set high. Any single error in the 16-bit data word will change the sense of exactly three bits of the 6-bit check word. Any single error in the 6-bit check word changes the sense of only that one bit. In either case, the single error flag will be set high while the dual error flag will remain low.

Any two-bit error will change the sense of an even number of check bits. The two-bit error is not correctable since the parity tree can only identify single-bit errors. Both error flags are set high when any two-bit error is detected.

Three or more simultaneous bit errors can fool the EDAC into believing that no error, a correctable error, or an uncorrectable error has occurred and produce erroneous results in all three cases.

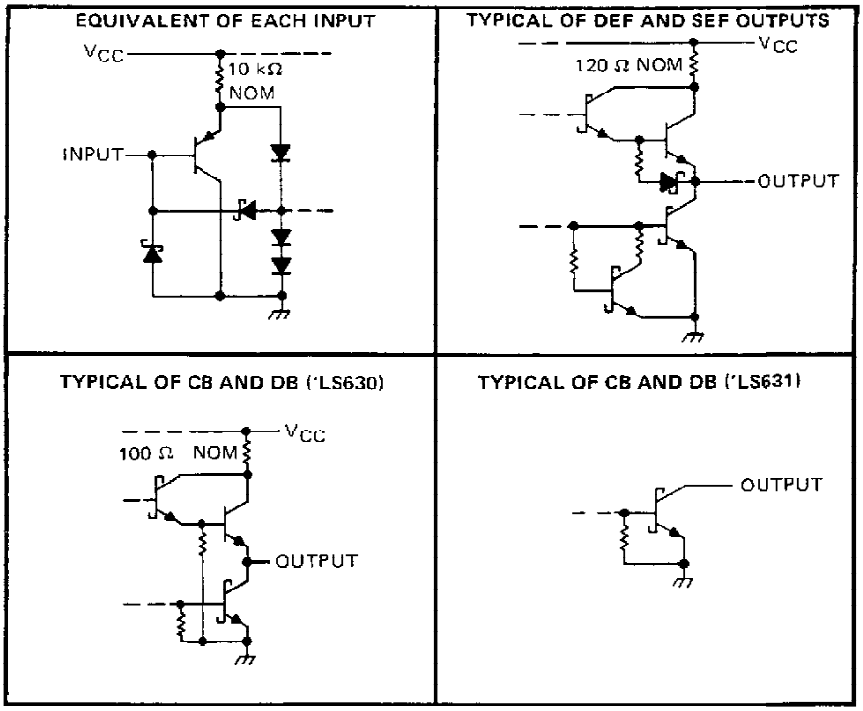
Error correction is accomplished by identifying the bad bit and inverting it. Identification of the erroneous bit is achieved by comparing the 16-bit data word and 6-bit check word from memory with the new check word with one (check word error) or three (data word error) inverted bits.

As the corrected word is made available on the data word I/O port, the check word I/O port presents a 6-bit syndrome error code. This syndrome code can be used to identify the bad memory chip.

ERROR SYNDROME TABLE

	SYNDROME ERROR CODE					
ERROR LOCATION	CB0	CB1	CB2	CB3	CB4	CB5
DB0	L	L	H	L	H	H
DB1	L	H	L	L	H	H
DB2	H	L	L	L	H	H
DB3	L	L	H	H	L	H
DB4	L	H	L	H	L	H
DB5	H	L	L	H	L	H
DB6	H	L	H	L	L	H
DB7	H	H	L	L	L	H
DB8	L	L	H	H	H	L
DB9	L	H	L	H	H	L
DB10	L	H	H	L	H	L
DB11	H	L	H	L	H	L
DB12	H	H	L	L	H	L
DB13	L	H	H	H	L	L
DB14	H	L	H	H	L	L
DB15	H	H	L	H	L	L
CB0	L	H	H	H	H	H
CB1	H	L	H	H	H	H
CB2	H	H	L	H	H	H
CB3	H	H	H	L	H	H
CB4	H	H	H	H	L	H
CB5	H	H	H	H	H	L
NO ERROR	H	H	H	H	H	H

schematics of inputs and outputs



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V_{CC} (see Note 1) . . . . . 7 V
Input voltage: S0 and S1 . . . . . 7 V
CB and DB . . . . . 5.5 V
Off-state output voltage . . . . . 5.5 V
Operating free-air temperature range: SN54LS630, SN54LS631 . . . . . −55°C to 125°C
SN74LS630, SN74LS631 . . . . . 0°C to 70°C
Storage temperature range . . . . . −65°C to 150°C

NOTE 1: Voltage Values are with respect to network ground terminal.

recommended operating conditions

		SN54LS630 SN54LS631			SN74LS630 SN74LS631			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
Supply voltage, V_{CC}		4.5	5	5.5	4.75	5	5.25	V
High-level output current, I_{OH}	CB or DB, 'LS630 only			−1			−1	mA
	DEF or SEF			−0.4			−0.4	
High-level output voltage, V_{OH}	CB or DB, 'LS631 only			5.5			5.5	V
Low-level output current, I_{OL}	CB or DB			12			24	mA
	DEF or SEF			4			8	
Setup time, t_{su}	CB or DB to S1↑	30			30			ns
Hold time, t_h	CB or DB after S1↑	15			15			ns
Operating free-air temperature, T_A		−55		125	0		70	°C

↑The upward-pointing arrow indicates a transition from low to high.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETERS			TEST CONDITIONS†		SN54LS630 MIN	SN54LS630 TYP‡	SN54LS630 MAX	SN74LS630 MIN	SN74LS630 TYP‡	SN74LS630 MAX	UNIT
V_{IH}	High-level input voltage				2			2			V
V_{IL}	Low-level input voltage						0.7			0.8	V
V_{IK}	Input clamp voltage		V_{CC} = MIN,	I_I = −18 mA			−1.5			−1.5	V
V_{OH}	High-level output voltage	CB or DB	V_{CC} = MIN, V_{IH} = 2 V, V_{IL} = V_{IL} min	I_{OH} = MAX	2.4	3.3		2.4	3.2		V
		DEF or SEF		I_{OH} = −400 μA	2.5	3.4		2.7	3.4		
V_{OL}	Low-level output voltage	CB or DB	V_{CC} = MIN, V_{IH} = 2 V, V_{IL} = V_{IL} max	I_{OL} = 12 mA		0.25	0.4		0.25	0.4	V
				I_{OL} = 24 mA					0.35	0.5	
		DEF or SEF		I_{OL} = 4 mA		0.25	0.4		0.25	0.4	
				I_{OL} = 8 mA					0.35	0.5	
I_{OZH}	Off-state output current, high-level voltage applied	CB or DB	V_{CC} = MAX, S0 and S1 at 2 V	V_O = 2.7 V,			20			20	μA
I_{OZL}	Off-state output current, low-level voltage applied	CB or DB	V_{CC} = MAX, S0 and S1 at 2 V	V_O = 0.4 V,			−200			−200	μA
I_I	Input current at maximum input voltage	CB or DB	V_{CC} = MAX, V_{IH} = 4.5 V	V_I = 5.5 V			0.1			0.1	mA
		S0 or S1		V_I = 7 V			0.1			0.1	
I_{IH}	High-level input current		V_{CC} = MAX,	V_I = 2.7 V			20			20	μA
I_{IL}	Low-level input current		V_{CC} = MAX,	V_I = 0.4 V			−0.2			−0.2	mA
I_{OS}	Short-circuit output current¶	CB or DB	V_{CC} = MAX		−30		−130	−30		−130	mA
		DEF or SEF			−20		−100	−20		−100	
I_{CC}	Supply current		V_{CC} = MAX, S0 and S1 at 4.5 V, All CB and DB pins grounded, DEF and SEF open			143	230		143	230	mA

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER			TEST CONDITIONS†		SN54LS631 MIN	SN54LS631 TYP‡	SN54LS631 MAX	SN74LS631 MIN	SN74LS631 TYP‡	SN74LS631 MAX	UNIT
V_{IH}	High-level input voltage				2			2			V
V_{IL}	Low-level input voltage						0.7			0.8	V
V_{IK}	Input clamp voltage		V_{CC} = MIN,	I_I = −18 mA			−1.5			−1.5	V
V_{OH}	High-level output voltage	DEF or SEF	V_{CC} = MIN, V_{IH} = 2 V,	I_{OH} = −400 μA, V_{IL} = V_{IL} max	2.5	3.4		2.7	3.4		V
I_{OH}	High-level output current	CB or DB	V_{CC} = MIN, V_{IH} = 2 V,	V_{OH} = 5.5 V, V_{IL} = V_{IL} max			100			100	μA
V_{OL}	Low-level output voltage	CB or DB	V_{CC} = MIN, V_{IH} = 2 V, V_{IL} = V_{IL} max	I_{OL} = 12 mA		0.25	0.4		0.25	0.4	V
				I_{OL} = 24 mA					0.35	0.5	
		DEF or SEF		I_{OL} = 4 mA		0.25	0.4		0.25	0.4	
				I_{OL} = 8 mA					0.35	0.5	
I_I	Input current at maximum input voltage	CB or DB	V_{CC} = MAX, V_{IH} = 4.5 V	V_I = 5.5 V			0.1			0.1	mA
		S0 or S1		V_I = 7 V			0.1			0.1	
I_{IH}	High-level input current		V_{CC} = MAX	V_I = 2.7 V			20			20	μA
I_{IL}	Low-level input current		V_{CC} = MAX,	V_I = 0.4 V			−0.2			−0.2	mA
I_{OS}	Short-circuit output current¶	DEF or SEF	V_{CC} = MAX		−20		−100	−20		−100	mA
I_{CC}	Supply current		V_{CC} = MAX, S0 and S1 at 4.5 V, All CB and DB grounded, SEF and DEF open			113	180		113	180	mA

† For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
‡ All typical values are at V_{CC} = 5 V, T_A = 25°C.
¶ Not more than one output should be shorted at a time, and duration of the short circuit should not exceed one second.

switching characteristics, V_{CC} = 5 V, T_A = 25°C, C_L = 45 pF

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	'LS630 MIN	'LS630 TYP	'LS630 MAX	UNIT
t_{PLH} Propagation delay time, low-to-high-level output◇	DB	CB	S0 at 0 V, S1 at 0 V, R_L = 667 Ω, See Figure 1		31	45	ns
t_{PHL} Propagation delay time, high-to-low-level output◇					45	65	ns
t_{PLH} Propagation delay time, low-to-high-level output*	S1↑	DEF	S0 at 3 V, R_L = 2 kΩ, See Figure 1		27	40	ns
		SEF			20	30	
t_{PZH} Output enable time to high level#	S0↓	CB, DB	S1 at 3 V, R_L = 667 Ω, See Figure 2		24	40	ns
t_{PZL} Output enable time to low level#	S0↓	CB, DB	S1 at 3 V, R_L = 667 Ω, See Figure 1		30	45	ns
t_{PHZ} Output disable time from high level▲	S0↑	CB, DB	S1 at 3 V, R_L = 667 Ω, See Figure 2		43	65	ns
t_{PLZ} Output disable time from low level▲	S0↑	CB, DB	S1 at 3 V, R_L = 667 Ω, See Figure 1		31	45	ns

switching characteristics, V_{CC} = 5 V, T_A = 25°C, C_L = 45 pF, see Figure 1

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	'LS631 MIN	'LS631 TYP	'LS631 MAX	UNIT
t_{PLH} Propagation delay time, low-to-high level output◇	DB	CB	S0 at 0 V, S1 at 0V, R_L = 667 Ω		38	55	ns
t_{PHL} Propagation delay time, high-to-low-level output◇					45	65	ns
t_{PLH} Propagation delay time, low-to-high-level output*	S1↑	DEF	S0 at 3 V, R_L = 2 kΩ		27	40	ns
		SEF			20	30	ns
t_{PHL} Propagation delay time, high-to-low-level output#	S0↓	CB, DB	S1 at 3 V, R_L = 667 kΩ		28	45	ns
t_{PLH} Propagation delay time, low-to-high-level output▲	S0↑	CB, DB	S1 at 3 V, R_L = 667 kΩ		33	50	ns

◇These parameters describe the time intervals taken to generate the check word during the memory write cycle.
*These parameters describe the time intervals taken to flag errors during the memory read cycle.
#These parameters describe the time intervals taken to correct and output the data word and to generate and output the syndrome error code during the memory read cycle.
▲These parameters describe the time intervals taken to disable the CB and DB buses in preparation for a new data word during the memory read cycle.

PARAMETER MEASUREMENT INFORMATION

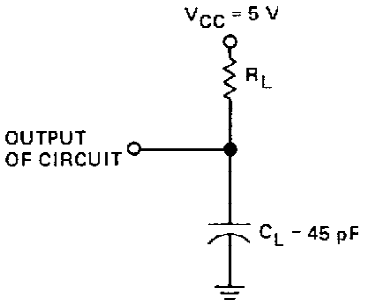


FIGURE 1–OUTPUT LOAD CIRCUIT

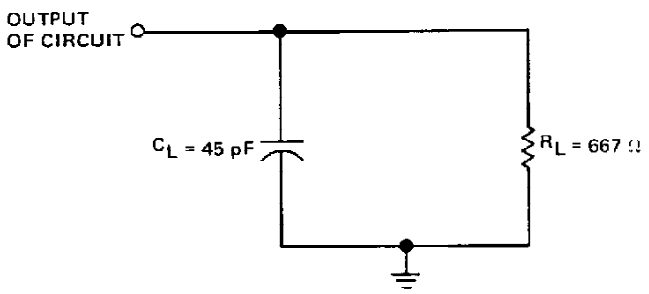


FIGURE 2–OUTPUT LOAD CIRCUIT

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